What is claimed is:

1. A method for manufacturing an electro-optical device, said method comprising the steps of:

forming a plurality of TFTs over a substrate;

forming a plurality of pixel electrodes each being connected to each of the plurality of TFTs; and

forming an EL layer over the plurality of pixel electrodes,

wherein the EL layer is selectively formed through an ink jet method.

2. A method for manufacturing an electro-optical device, said method comprising the steps of:

forming a plurality of TFTs over a substrate;

forming a plurality of pixel electrodes each being connected to each of the plurality of TFTs; and

forming an EL layer over the plurality of pixel electrodes,

wherein the EL layer is selectively formed through an ink jet method corresponding to each of the plurality of pixel electrodes.

3. A method for manufacturing an electro-optical device, said method comprising the steps of:

forming a plurality of TFTs over a substrate;

forming a plurality of pixel electrodes each being connected to each of the plurality of TFTs;

forming a first EL layer that emits red-colored light over

a pixel electrode disposed on a pixel that corresponds to red among the plurality of pixel electrodes;

forming a second EL layer that emits green-colored light over a pixel electrode disposed on a pixel that corresponds to green among the plurality of pixel electrodes; and

forming a third EL layer that emits blue-colored light over a pixel electrode disposed on a pixel that corresponds to blue among the plurality of pixel electrodes,

wherein each of the first, second and third EL layers is selectively formed through an ink jet method.

4. A method for manufacturing an electro-optical device, said method comprising the steps of:

forming a plurality of TFTs over a substrate;

forming an insulating film covering the plurality of TFTs;

forming a plurality of openings in the insulating film;

forming a plurality of pixel electrodes each being connected to each of the plurality of TFTs; and

forming an EL layer selectively through an ink jet method over the plurality of pixel electrodes,

wherein an uppermost layer of the insulating film is capable of preventing penetration of an alkaline metal.

5. A method for manufacturing an electro-optical device comprising the steps of:

forming a plurality of TFTs over a substrate;

forming an insulating film covering the plurality of TFTs;

forming a plurality of openings in the insulating film;

forming a plurality of pixel electrodes each being connected to each of the plurality of TFTs; and

forming an EL layer over the plurality of pixel electrodes through an ink jet method selectively corresponding to each of the plurality of pixel electrodes,

wherein an uppermost layer of the insulating film is capable of preventing penetration of an alkaline metal.

6. A method for manufacturing an electro-optical device, said method comprising the steps of:

forming a plurality of TFTs over a substrate;

forming an insulating film covering the plurality of TFTs;

forming a plurality of openings in the insulating film;

forming a plurality of pixel electrodes each being connected to each of the plurality of TFTs; and

forming a first EL layer that emits red-colored light over a pixel electrode disposed on a pixel that corresponds to red among the plurality of pixel electrodes;

forming a second EL layer that emits green-colored light over a pixel electrode disposed on a pixel that corresponds to green among the plurality of pixel electrodes; and

forming a third EL layer that emits blue-colored light over a pixel electrode disposed on a pixel that corresponds to blue among the plurality of pixel electrodes,

wherein each of the first, second and third EL layers is selectively formed through an ink jet method, and

wherein an uppermost layer of the insulating film is capable of preventing penetration of an alkaline metal.

7. A method according to claim 3,

wherein the pixel that corresponds to red, the pixel that corresponds to green and the pixel that corresponds to blue are formed in contact with each other.

8. A method according to claim 1,

wherein the EL layer is an organic material.

9. A method according to claim 1,

wherein the ink jet method uses a piezo element.

10. A method according to claim 4,

wherein the insulating film comprises:

an organic resin film;

an insulating layer being capable of preventing penetration of an alkaline metal on the organic resin film.

11. A method according to claim 4,

wherein the insulating film comprising at least one of the elements selected from a group consisting of B (boron), C (carbon)

and N (nitrogen) and at least one of the elements selected from a group consisting of Al (aluminum), Si (silicon) and P (phosphorus).

12. A method according to claim 4,

wherein the insulating film comprises Si, Al, N, O and M,

wherein M is at least an element selected from a rare-earth element, preferably an element selected from the group consisting of Ce (cesium), Yb (ytterbium), Sm (samarium), Er (erbium), Y (yttrium), La (lanthanum), Gd (gadolinium), Dy (dysprosium), and Nd (neodymium)).

13. A method according to claim 2,

wherein the EL layer is an organic material.

14. A method according to claim 2,

wherein the ink jet method uses a piezo element.

15. A method according to claim 3,

wherein the EL layer is an organic material.

16. A method according to claim 3,

wherein the ink jet method uses a piezo element.

17. A method according to claim 4,

wherein the EL layer is an organic material.

18. A method according to claim 4,

wherein the ink jet method uses a piezo element.

19. A method according to claim 5,

wherein the EL layer is an organic material.

20. A method according to claim 5,

wherein the ink jet method uses a piezo element.

21. A method according to claim 5,

wherein the insulating film comprises:

an organic resin film;

an insulating layer being capable of preventing penetration of an alkaline metal on the organic resin film.

22. A method according to claim 5,

wherein the insulating film comprising at least one of the elements selected from a group consisting of B (boron), C (carbon) and N (nitrogen) and at least one of the elements selected from a group consisting of Al (aluminum), Si (silicon) and P (phosphorus).

23. A method according to claim 5,

wherein the insulating film comprises Si, Al, N, O and M,

wherein M is at least an element selected from a rare-earth element, preferably an element selected from the group consisting of Ce (cesium), Yb (ytterbium), Sm (samarium), Er (erbium), Y (yttrium), La (lanthanum), Gd (gadolinium), Dy (dysprosium), and Nd (neodymium)).

24. A method according to claim 6,

wherein the pixel that corresponds to red, the pixel that corresponds to green and the pixel that corresponds to blue are formed in contact with each other.

25. A method according to claim 6,

wherein the EL layer is an organic material.

26. A method according to claim 6,

wherein the ink jet method uses a piezo element.

27. A method according to claim 6,

wherein the insulating film comprises:

an organic resin film;

an insulating layer being capable of preventing penetration of an alkaline metal on the organic resin film.

28. A method according to claim 6,

wherein the insulating film comprising at least one of the elements selected from a group consisting of B (boron), C (carbon) and N (nitrogen) and at least one of the elements selected from a group consisting of Al (aluminum), Si (silicon) and P (phosphorus).

29. A method according to claim 6,

wherein the insulating film comprises Si, Al, N, O and M,

wherein M is at least an element selected from a rare-earth element, preferably an element selected from the group consisting of Ce (cesium), Yb (ytterbium), Sm (samarium), Er (erbium), Y (yttrium), La (lanthanum), Gd (gadolinium), Dy (dysprosium), and Nd (neodymium)).